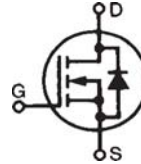


High Voltage Power MOSFET

IXTT1N300P3HV IXTH1N300P3HV

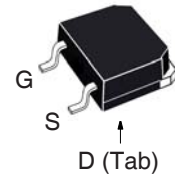
$$\begin{aligned} V_{DSS} &= 3000V \\ I_{D25} &= 1.00A \\ R_{DS(on)} &\leq 50\Omega \end{aligned}$$

N-Channel Enhancement Mode

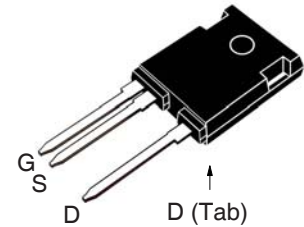


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	3000	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	3000	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	1.00	A
I_{D110}	$T_C = 110^\circ\text{C}$	0.65	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	2.60	A
P_D	$T_C = 25^\circ\text{C}$	195	W
T_J		- 55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		- 55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-247)	1.13/10	Nm/lb.in
Weight	TO-268HV	4.0	g
	TO-247HV	6.0	g

TO-268HV (IXTT)



TO-247HV (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Features

- High Blocking Voltage
- High Voltage Packages

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	3000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5A$, Note 1			50 Ω

Symbol	Test Conditions	Characteristic Values		
	(T _J = 25°C, Unless Otherwise Specified)	Min.	Typ.	Max.
g_{fs}	V _{DS} = 50V, I _D = 0.5A, Note 1	0.4	0.7	S
C_{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		895	pF
C_{oss}			48	pF
C_{rss}			17	pF
t_{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 500V, I _D = 0.5 • I _{D25} R _G = 20Ω (External)		22	ns
t_r			35	ns
t_{d(off)}			78	ns
t_f			60	ns
Q_{g(on)}	V _{GS} = 10V, V _{DS} = 1kV, I _D = 0.5 • I _{D25}		30.6	nC
Q_{gs}			4.0	nC
Q_{gd}			15.7	nC
R_{thJC}	TO-247HV		0.64 °C/W	°C/W
R_{thCS}		0.21		

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
	(T _J = 25°C, Unless Otherwise Specified)	Min.	Typ.	Max.
I_S	V _{GS} = 0V			1.0 A
I_{SM}	Repetitive, Pulse Width Limited by T _{JM}			4.0 A
V_{SD}	I _F = I _S , V _{GS} = 0V, Note 1			1.5 V
t_{rr}	I _F = 1A, -di/dt = 100A/μs, V _R = 100V		1.8	μs

Note: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

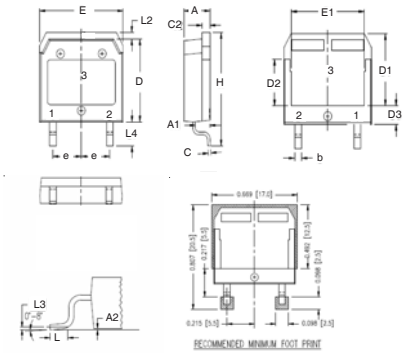
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

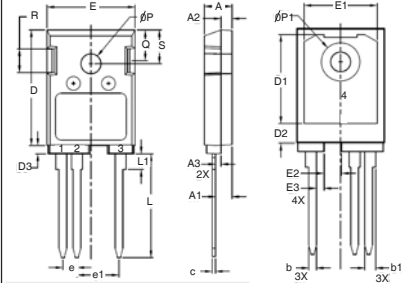
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-268HV Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
E2	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

TO-247HV Outline



PINS:
1 - Gate 2 - Source
3, 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100	BSC	2.54	BSC
e1	.300	BSC	7.62	BSC
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
øP	.138	.142	3.50	3.60
øP1	.272	.280	6.90	7.10
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30
S	.240	.248	6.10	6.30

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

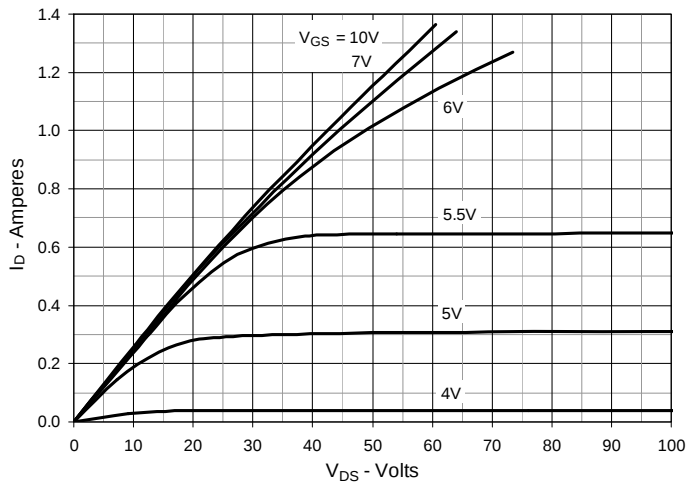


Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

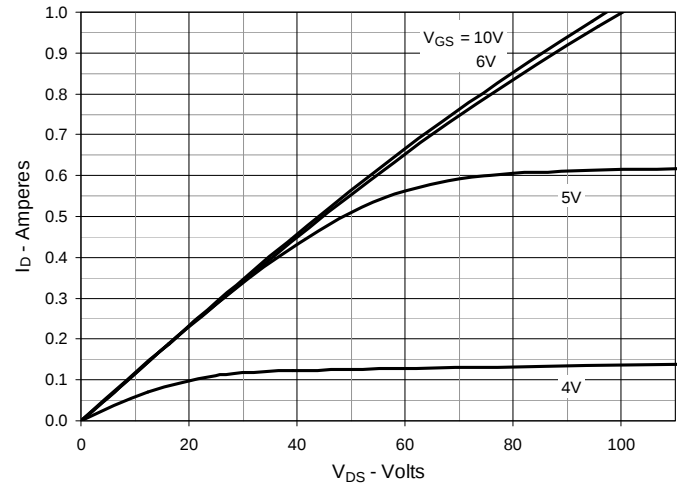


Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 0.5\text{A}$ Value vs. Junction Temperature

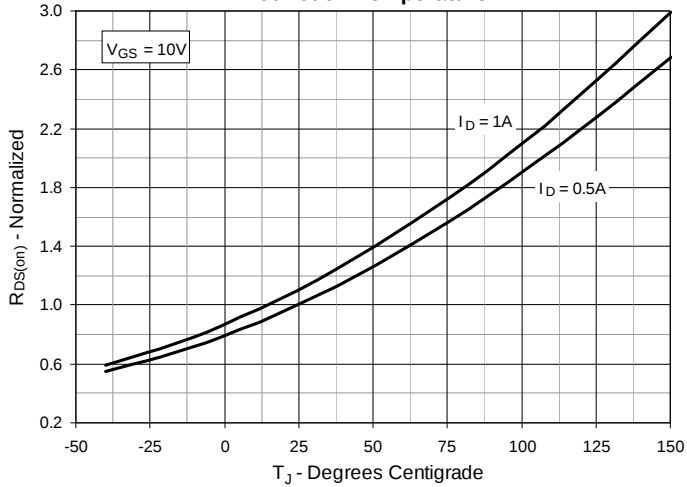


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 0.5\text{A}$ Value vs. Drain Current

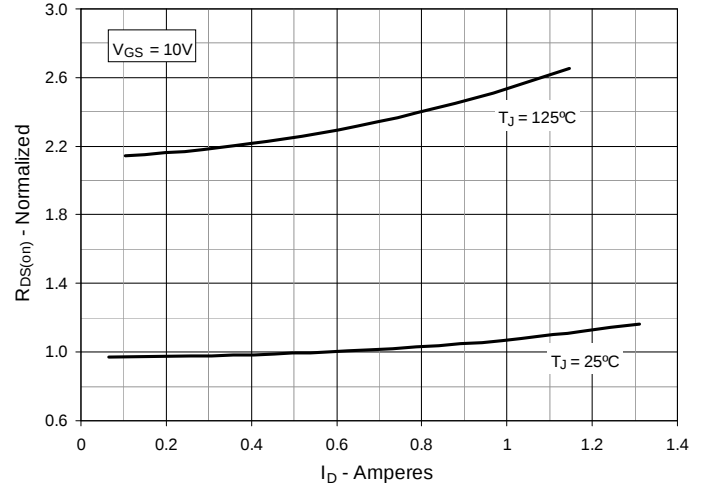


Fig. 5. Maximum Drain Current vs. Case Temperature

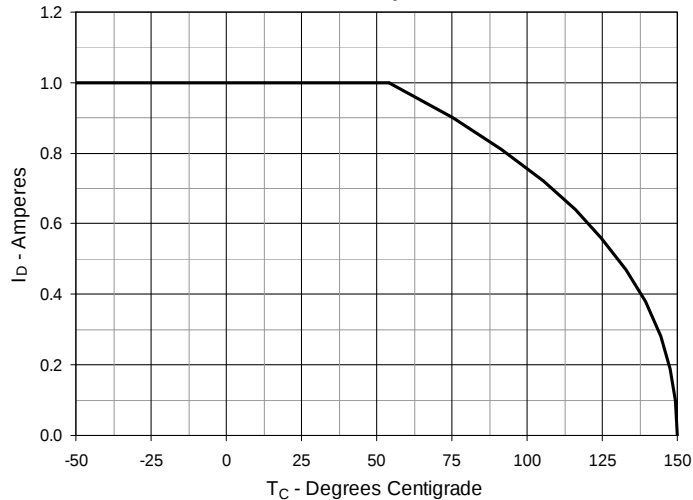


Fig. 6. Input Admittance

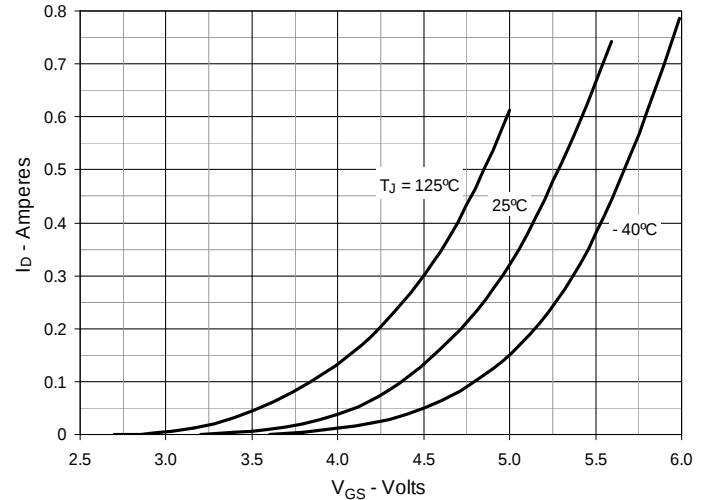


Fig. 7. Transconductance

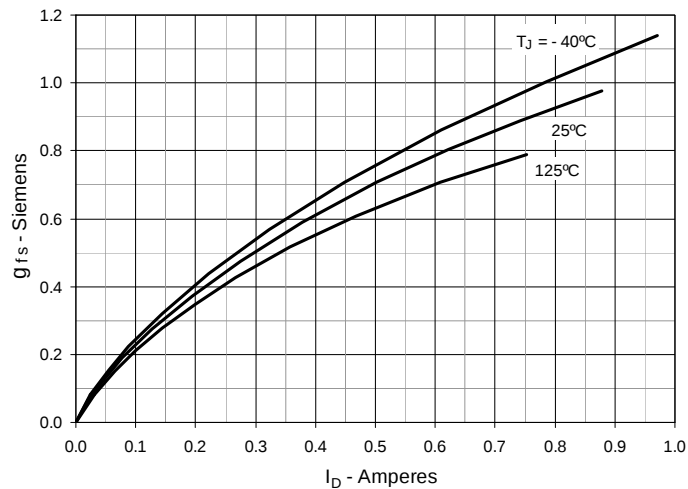


Fig. 8. Forward Voltage Drop of Intrinsic Diode

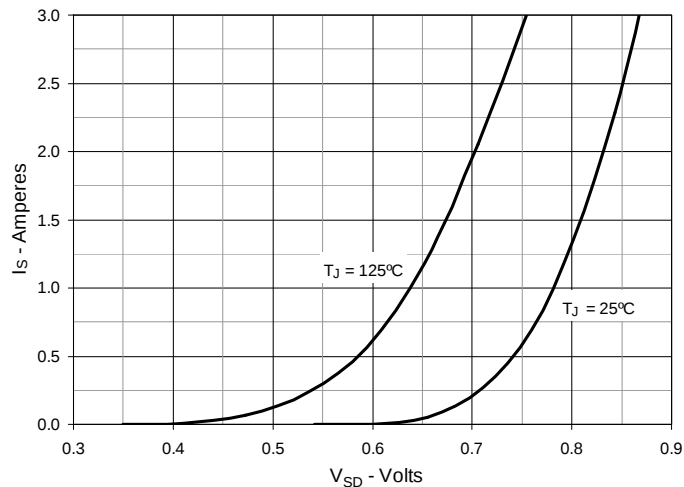


Fig. 9. Gate Charge

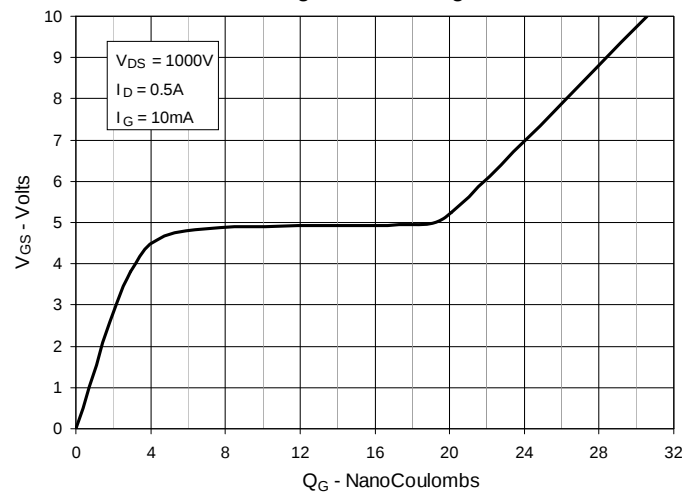


Fig. 10. Capacitance

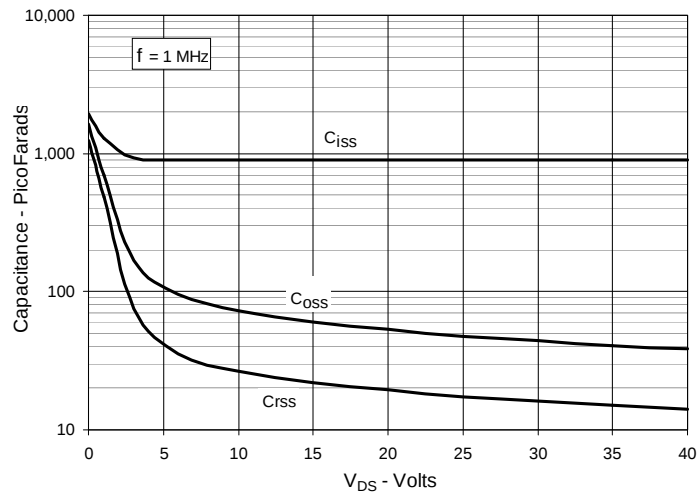


Fig. 11. Maximum Transient Thermal Impedance

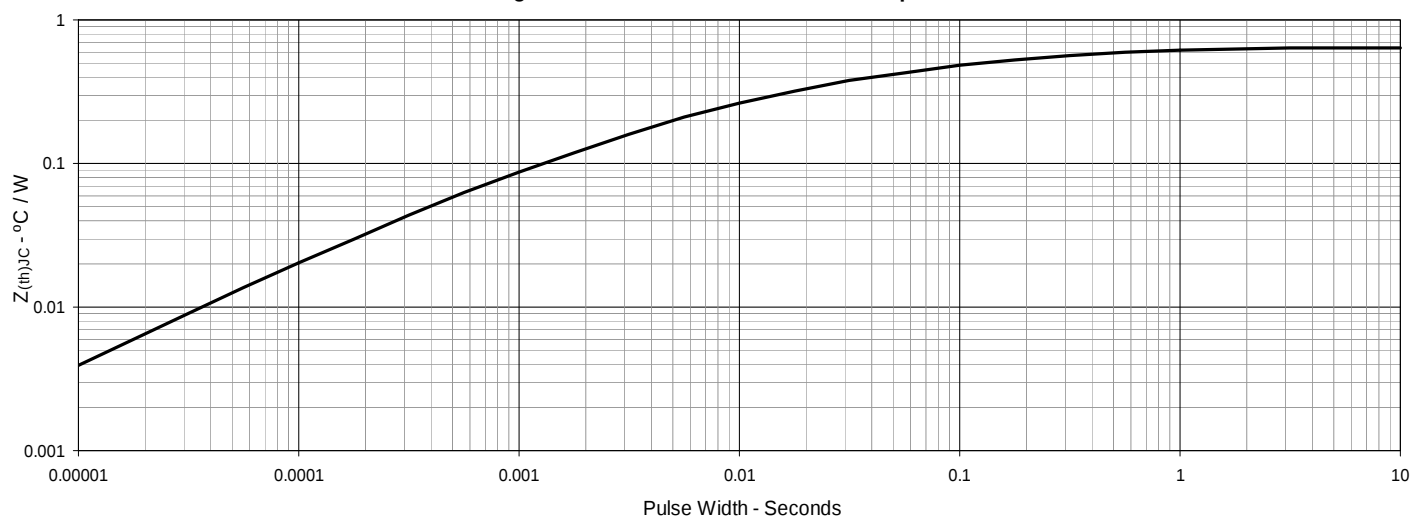


Fig. 12. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

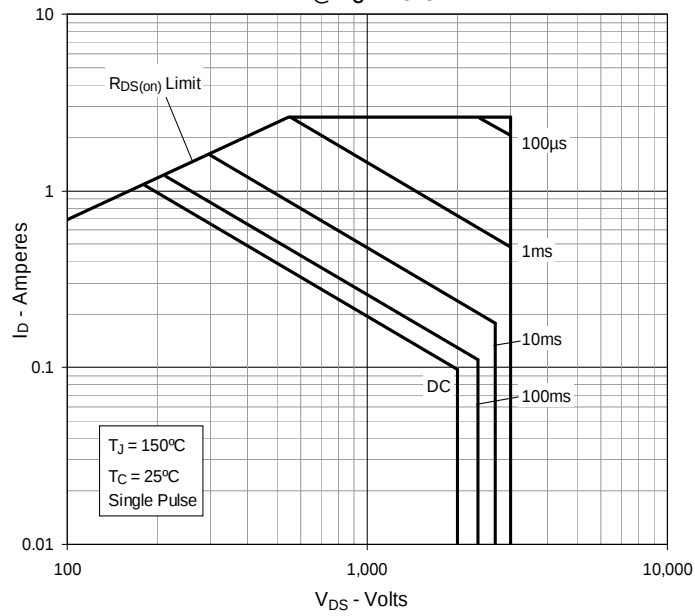


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$

